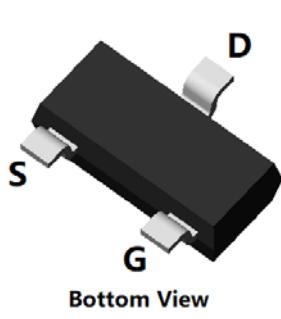
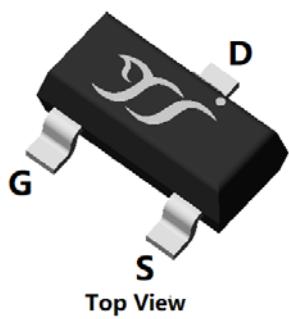
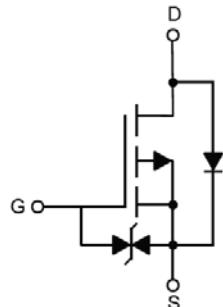


P-Channel Enhancement Mode Field Effect Transistor


SOT-23


Product Summary

- V_{DS} -20 V
- I_D - 3.9A
- $R_{DS(on)}$ (at $V_{GS}=-4.5V$) <45 mΩ
- $R_{DS(on)}$ (at $V_{GS}=-2.5V$) <75 mΩ
- ESD Protected Up to 2.0KV (HBM)

General Description

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Part no. with suffix "Q" means AEC-Q101 qualified
- Halogen Free

Applications

- Power management
- Portable equipment

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	± 10	V
Drain Current	$T_A=25^\circ C$	I_D	-3.9	A
	$T_A=100^\circ C$		-2.4	
Pulsed Drain Current ^A		I_{DM}	-23	A
Total Power Dissipation ^C	$T_A=25^\circ C$	P_D	1	W
	$T_A=100^\circ C$		0.4	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	°C

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	100	120	°C/W

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3415KCQ	F2	3415C	3000	30000	120000	7" reel



YJL3415KCQ

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
		$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}, T_J=150^\circ\text{C}$	-	-	-100	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 10\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 10	μA
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.5	-0.85	-1.25	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-3.9\text{A}$	-	28	45	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-2\text{A}$	-	50	75	$\text{m}\Omega$
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=-3.9\text{A}, V_{\text{GS}}=0\text{V}$	-	-0.9	-1.2	V
Gate resistance	R_{G}	f=1MHz, Open drain	-	17	-	Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	540	-	pF
Output Capacitance	C_{oss}		-	120	-	
Reverse Transfer Capacitance	C_{rss}		-	100	-	
Switching Parameters						
Total Gate Charge	Q_{g}	$V_{\text{GS}}=-10\text{V}, V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-5\text{A}$	-	13	-	nC
Gate-Source Charge	Q_{gs}		-	2	-	
Gate-Drain Charge	Q_{gd}		-	2	-	
Reverse Recovery Charge	Q_{rr}	$I_{\text{F}}=-5\text{A}, \text{di}/\text{dt}=100\text{A}/\text{us}$	-	2.5	-	nC
Reverse Recovery Time	t_{rr}		-	20	-	ns
Turn-on Delay Time	$t_{\text{D}(\text{on})}$	$V_{\text{GS}}=-10\text{V}, V_{\text{DD}}=-10\text{V}, I_{\text{D}}=-5\text{A}$ $R_{\text{GEN}}=2.2\Omega$	-	5	-	ns
Turn-on Rise Time	t_{r}		-	47	-	
Turn-off Delay Time	$t_{\text{D}(\text{off})}$		-	52	-	
Turn-off fall Time	t_{f}		-	69	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. P_d is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.

C. The value of R_{GJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in the still air environment with $T_A = 25^\circ\text{C}$.

The maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.

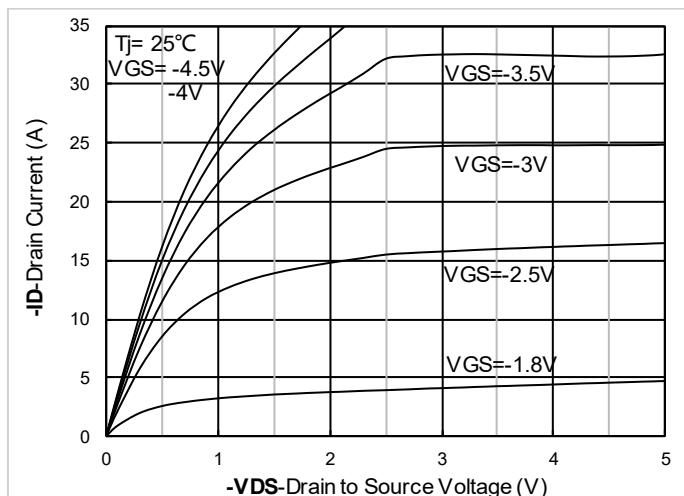
**■Typical Electrical and Thermal Characteristics Diagrams**

Figure 1. Output Characteristics

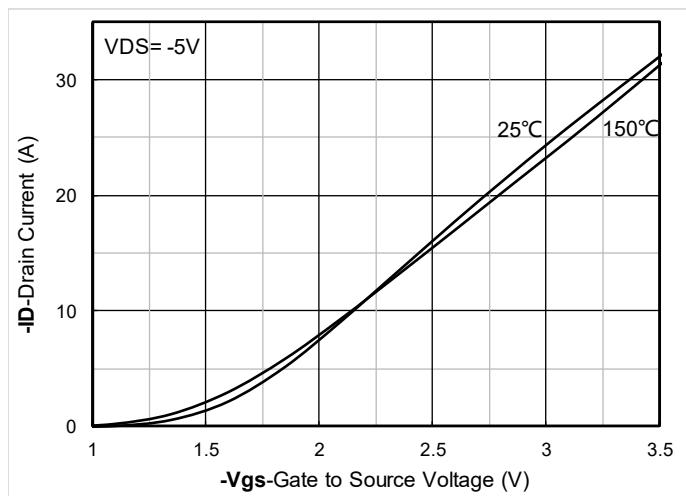


Figure 2. Transfer Characteristics

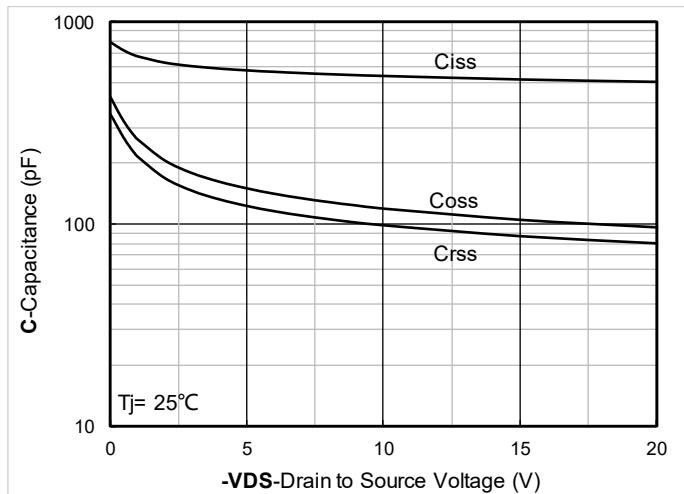


Figure 3. Capacitance Characteristics

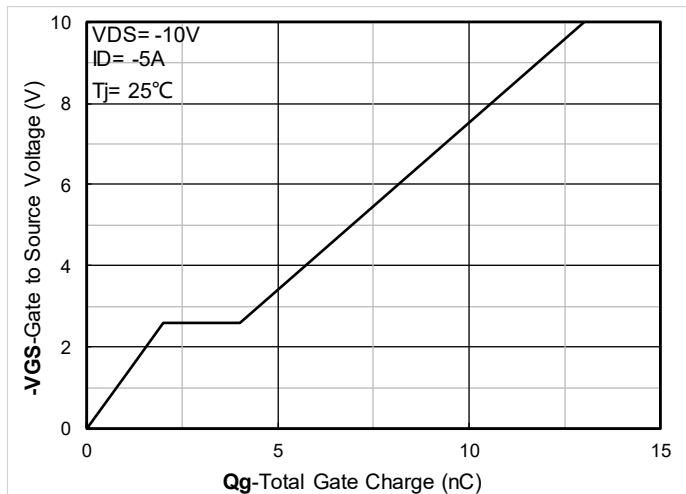


Figure 4. Gate Charge

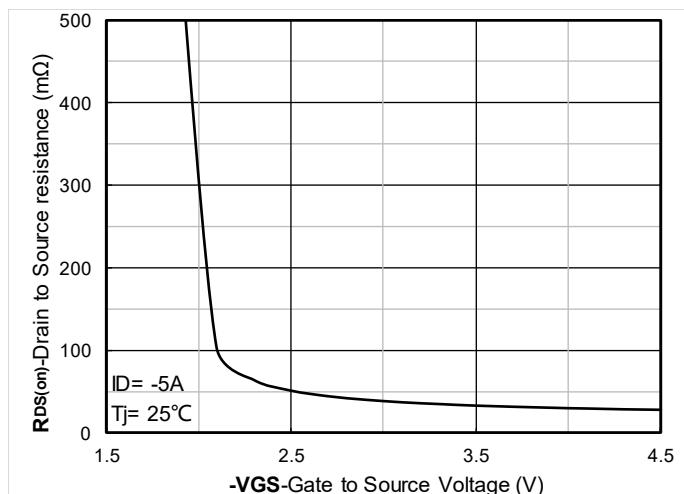


Figure 5. On-Resistance vs Gate to Source Voltage

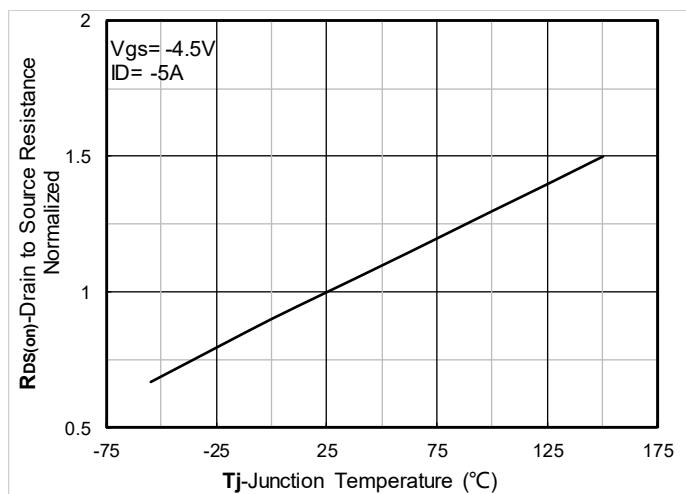


Figure 6. Normalized On-Resistance

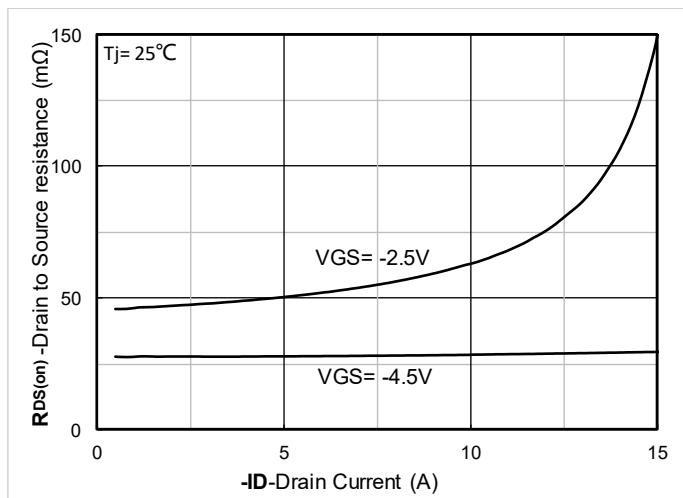


Figure 7. $R_{DS(on)}$ VS Drain Current

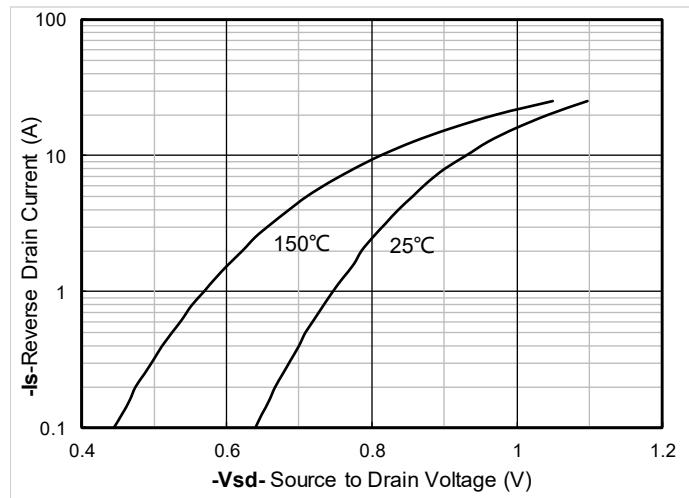


Figure 8. Forward characteristics of reverse diode

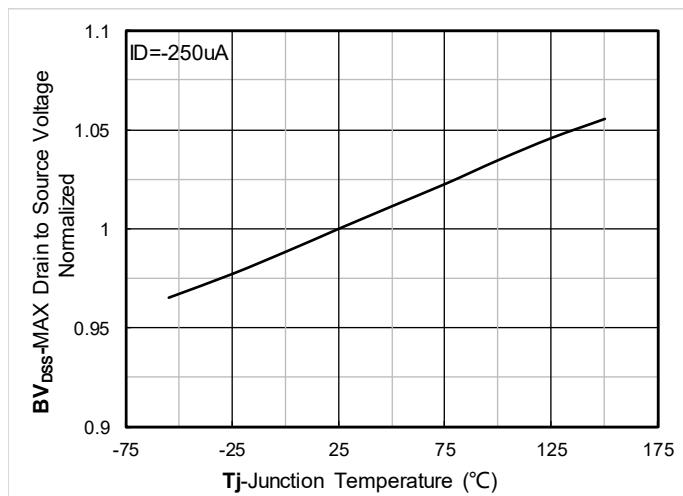


Figure 9. Normalized breakdown voltage

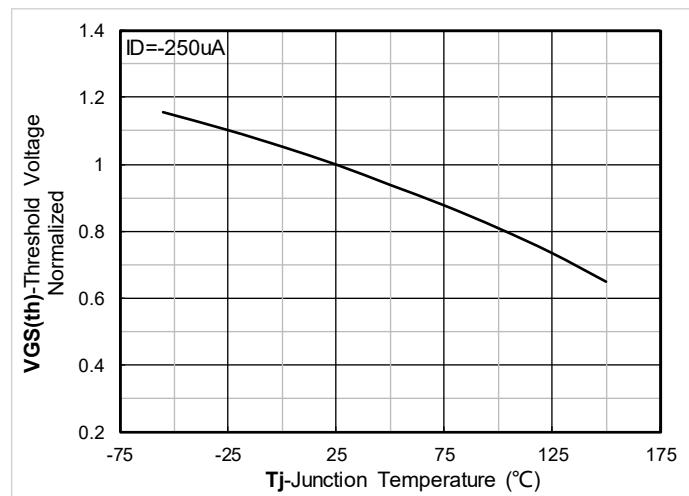


Figure 10. Normalized Threshold voltage

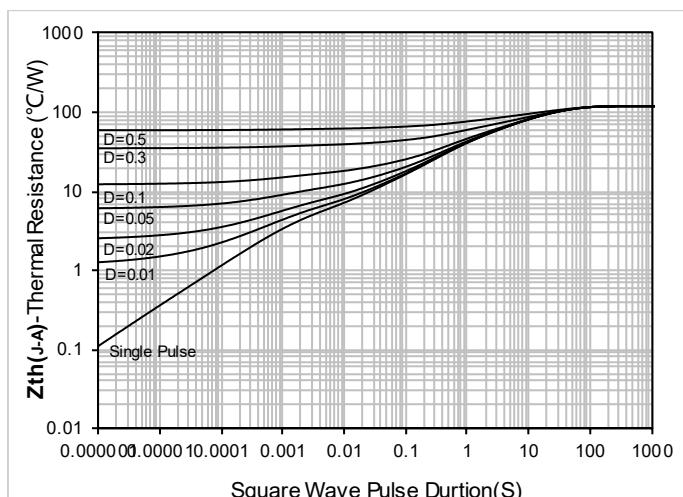


Figure 11. Maximum Transient Thermal Impedance

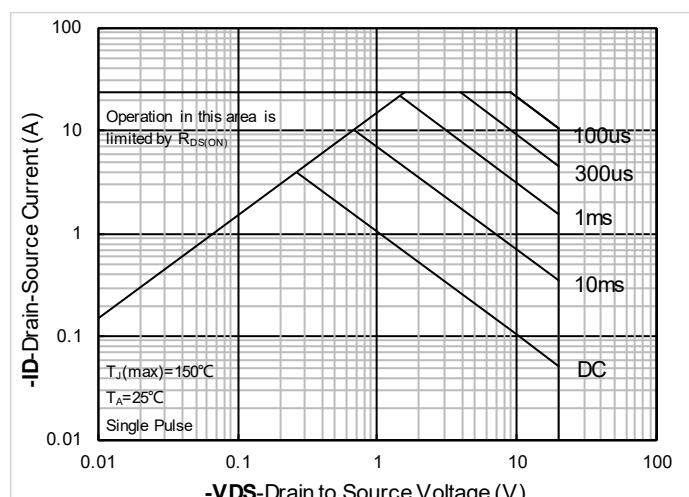
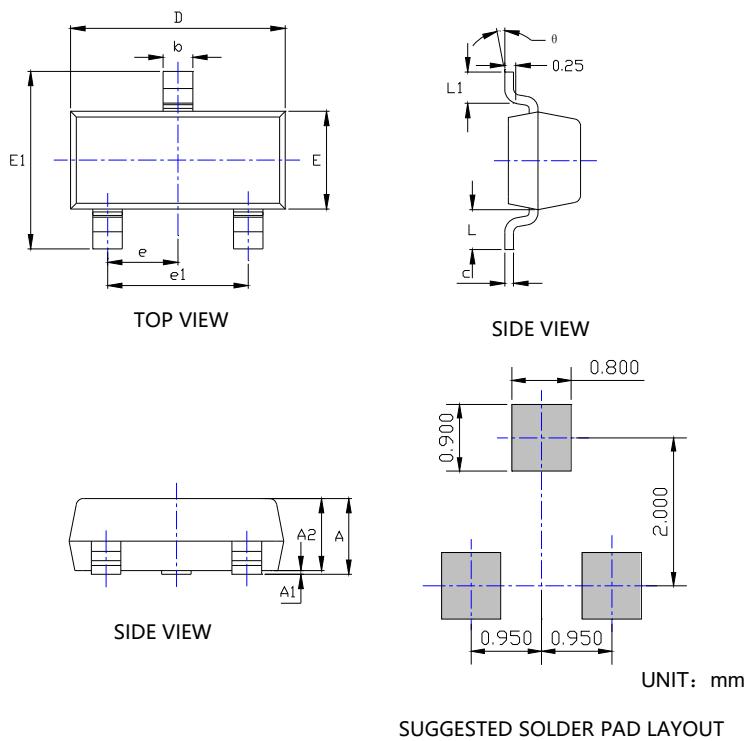


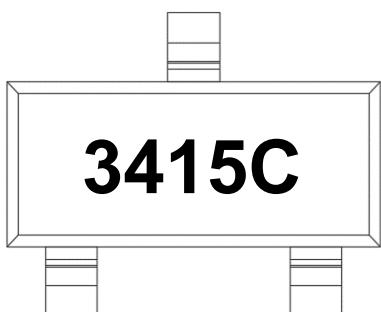
Figure 12. Safe Operation Area

**■ SOT-23 Package information**

SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.045	0.900	1.150
A1	0.000	0.004	0.000	0.100
A2	0.035	0.041	0.900	1.050
b	0.012	0.020	0.300	0.500
c	0.004	0.008	0.100	0.200
D	0.110	0.118	2.800	3.000
E	0.047	0.055	1.200	1.400
E1	0.089	0.100	2.250	2.550
e	0.037TYP		0.950TYP	
e1	0.071	0.079	1.800	2.000
L	0.022REF		0.550REF	
L1	0.012	0.020	0.300	0.500
theta	0°	8°	0°	8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

■ Marking Information

Note:

1. All marking is at middle of the product body
2. All marking is in laser marking
3. 3415C is Marking Code
4. Body color: Black



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